

安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD

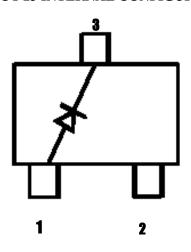
BZX84C3V0-C47

SOT-23 SURFACE MOUNT ZENER DIODE 表面貼裝穩壓二極管

■FEATURES 特點

Characteristic 特性參數	Symbol 符號	Max 最大値	Unit 單位	
Power dissipation 耗散功率	P _D (Ta=25°C)	300	mW	
Forward Current 正向電流	I_{F}	250	mA	
Forward Voltage 正向電壓	V _F (@ I _F =10mA)	0.9	V	
Reverse Voltage 反向電壓	V_z	3-47	V	
Junctoin and Storage Temperature 結溫和儲藏溫度	$T_{ m J}, T_{ m stg}$	125°C,-55to+125°C		

■SOT-23 INTERNAL CONFIGURATION 內部結構





安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD

■ELECTRICAL CHARACTERISTICS 電特性

(T_{A} =25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

CHARACTERISTICS			DIFFER	DIFFERENTIAL RESISTANCE $ m r_{dif}(\Omega)$		TEMP. COEFF. S _Z (mV/K)		Marking		
TEST CONDITION			I _Z =1	I _Z =1mA		I _Z =5mA		I _Z =5mA		
	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	
BZX84C3V0	2.8	3.2	325	600	80	95	-3.5	-2.1	0	Z13
BZX84C3V3	3.1	3.5	350	600	85	95	-3.5	-2.4	0	Z14
BZX84C3V6	3.4	3.8	375	600	85	90	-3.5	-2.4	0	Z15
BZX84C3V9	3.7	4.1	400	600	85	90	-3.5	-2.5	0	Z16
BZX84C4V3	4.0	4.6	400	600	85	90	-3.5	-2.5	0	Z17
BZX84C4V7	4.4	5.0	410	600	80	90	-3.5	-2.5	0	Z1
BZX84C5V1	4.8	5.4	425	500	50	80	-3.5	-1.4	0.2	Z2
BZX84C5V6	5.2	6.0	400	480	40	60	-2.7	-0.8	1.2	Z3
BZX84C6V2	5.8	6.6	80	400	15	40	-2.0	1.2	2.5	Z4
BZX84C6V8	6.4	7.2	40	150	6	10	0.4	2.3	3.7	Z5
BZX84C7V5	7.0	7.9	30	80	6	15	1.2	3.0	4.5	Z6
BZX84C8V2	7.7	8.7	30	80	6	15	2.5	4.0	5.3	Z7
BZX84C9V1	8.5	9.6	40	80	6	15	3.2	4.6	6.2	Z8
BZX84C10	9.4	10.6	40	100	6	15	3.8	5.5	7.0	Z9
BZX84C11	10.4	11.6	50	150	8	20	4.5	6.4	8.0	Y1
BZX84C12	11.4	12.7	50	150	10	20	5.4	7.4	9.0	Y2
BZX84C13	12.4	14.1	50	150	10	25	6.0	8.4	10.0	Y3
BZX84C15	13.8	15.6	50	170	10	30	7.0	9.4	11.0	Y4
BZX84C16	15.3	17.1	50	200	10	30	9.2	11.4	13.0	Y5
BZX84C18	16.8	19.1	50	200	10	40	10.4	12.4	14.0	Y6
BZX84C20	18.8	21.2	50	225	10	45	12.4	14.4	16.0	Y7
BZX84C22	20.8	23.3	60	225	15	55	14.4	16.4	18.0	Y8
BZX84C24	22.8	25.6	60	250	20	55	16.4	18.4	20.0	Y9
TEST CONDITION	I _z =2	2mA	I _Z =0.5mA							
BZX84C27	25.1	28.9	65	300	25	80	21.4	23.4	25.3	Y10
BZX84C30	28.0	32.0	70	300	30	80	24.4	26.6	29.4	Y11
BZX84C33	31.0	35.0	75	325	35	80	27.4	29.7	33.4	Y12
BZX84C36	34.0	38.0	80	350	35	90	30.4	33.0	37.4	Y13
BZX84C39	37.0	41.0	80	350	40	130	33.4	36.4	41.2	Y14
BZX84C43	40.0	46.0	85	375	45	150	37.6	41.2	46.6	Y15
BZX84C47	44.0	50.0	85	375	50	170	42.0	46.1	51.8	Y16

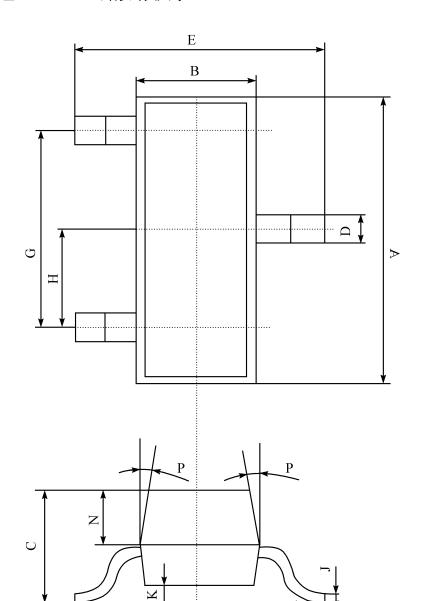


安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD

BZX84C3V0-C47

■DIMENSION 外形封裝尺寸



序號	數值及公差
A	2.90 ± 0.10
В	1.30 ± 0.10
С	1.00 ± 0.10
D	0.40 ± 0.10
Е	2.40 ± 0.20
G	1.90 ± 0.10
Н	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00-0.10
M	≥0.2
N	0.60 ± 0.10
P	7 ± 2°